



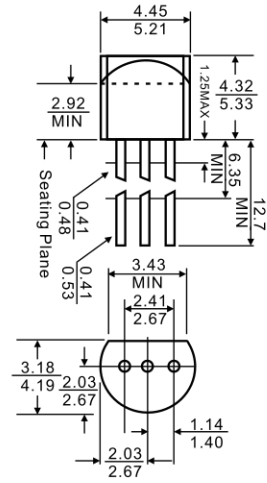
1. EMITTER
2. BASE
3. COLLECTOR

GENERAL PURPOSE APPLICATIONS.
DARLINGTON TRANSISTOR.

MAXIMUM RATING (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	30	V
Collector-Emitter Voltage	V_{CES}	30	V
Emitter-Base Voltage	V_{EBO}	10	V
Collector Current	I_C	500	mA
Collector Power Dissipation	P_C	625	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55 ~ 150	°C

TO-92

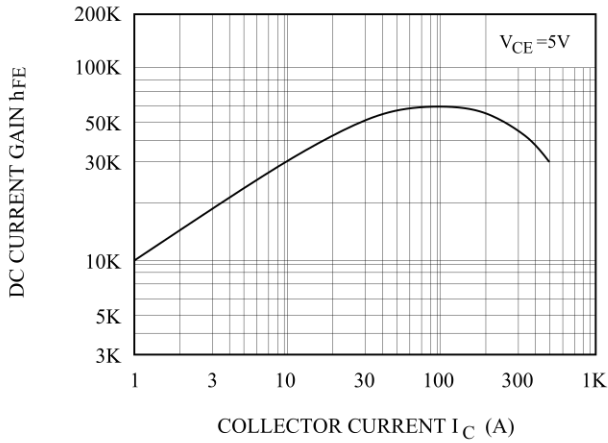


Dimensions in inches and (millimeters)

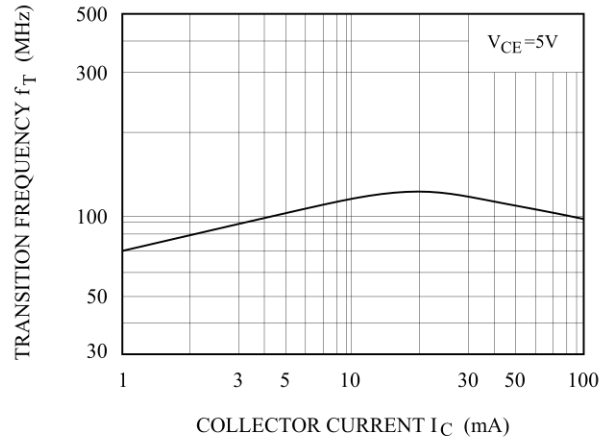
ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector-Emitter Breakdown Voltage		V_{CES}	$I_C=0.1mA$	30	-	-	V
Emitter Cut-off Current		I_{CBO}	$V_{CB}=30V$	-	-	100	nA
Emitter Cut-off Current		I_{EBO}	$V_{EB}=10V$	-	-	100	nA
DC Current Gain	MPSA13	h_{FE}	$I_C=10mA, V_{CE}=5V$	5,000	-	-	-
	MPSA14			10,000	-	-	
	MPSA13		$I_C=100mA, V_{CE}=5V$	10,000	-	-	
	MPSA14			20,000	-	-	
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	$I_C=100mA, I_B=0.1mA$	-	-	1.5	V
Base-Emitter Voltage		V_{BE}	$I_C=100mA, V_{CE}=5V$	-	-	2.0	V
Current Gain Bandwidth Product		f_T	$I_C=10mA, f=100MHz, V_{CE}=5V$	125	-	-	MHz

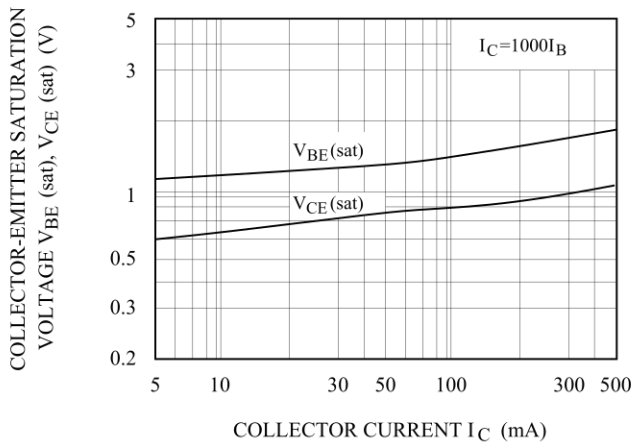
$h_{FE} - I_C$



$f_T - I_C$



$V_{BE} (sat), V_{CE} (sat) - I_C$



$I_C - V_{BE}$

